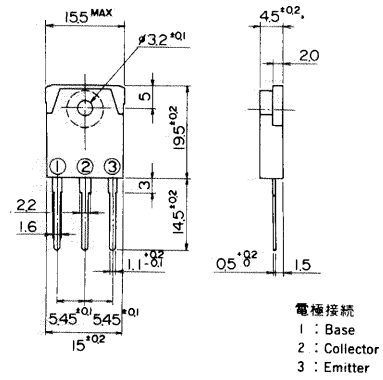
2SC3550

FUJI POWER TRANSISTOR

TRIPLE DIFFUSED PLANER TYPE
HIGH VOLTAGE,HIGH SPEED SWITCHING

■ Outline Drawings

TO-3P



JEDEC	-
EIAJ	SC-65

■ Features

- **High voltage,High speed switching**
- **High reliability**

■ Applications

- **Switching regulators**
- **Ultrasonic generators**
- **High frequency inverters**
- **General purpose power amplifiers**

■ Maximum ratings and characteristics

● **Absolute maximum ratings (Tc=25°C unless otherwise specified)**

Item	Symbol	Ratings	Unit
Collector-Base voltage	V_{CBO}	900	V
Collector-Emitter voltage	V_{CEO}	800	V
Collector-Emitter voltage	$V_{CEO(SUS)}$	-	V
Emitter-Base voltage	V_{EBO}	10	V
Collector current	I_C	3	A
Base current	I_B	1	A
Collector power disspation	P_C	80	W
Operating junction temperature	T_j	+150	℃
Storage temperature	T_{stg}	-55 to +150	℃

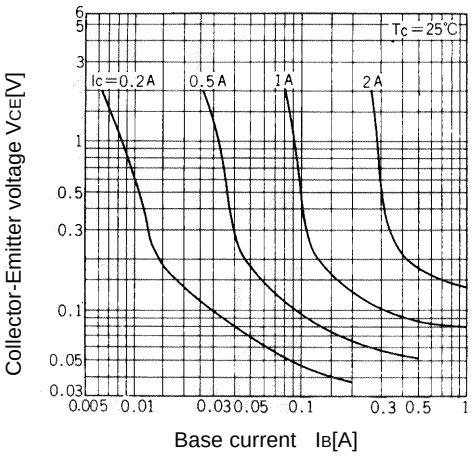
● **Electrical characteristics (T_C =25°C unless otherwise specified)**

Item	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Collector-Base voltage	V_{CBO}	I_{CBO} = 1mA	900			V
Collector-Emitter voltage	V_{CEO}	I_{CEO} = 10mA	800			V
Collector-Emitter voltage	$V_{CEO(SUS)}$	I_C = A	-	-		V
Emitter-Base voltage	V_{EBO}	I_{EBO} = 1mA	10	-		V
Collector-Base leakage current	I_{CBO}	V_{CBO} = 900V		-	1.0	mA
Emitter-Base leakage current	I_{EBO}	V_{EBO} = 10V		-	1.0	mA
D.C. current gain	h_{FE}	I_C = 1A, V_{CE} = 5V	10			
Collector-Emitter saturation voltage	$V_{CE(Sat)}$	I_C = 1A, I_B = 0.2A			1.0	V
Base-Emitter saturation voltage	$V_{BE(Sat)}$				1.5	V
*1	t_{on}	I_C = 1A, I_{B1} = 0.4A			1.0	µs
Switching time	t_{stg}	I_{B2} = -0.8A, R_L = 150 ohm			4.0	µs
	t_f	Pw = 20 µs Duty=<2%			0.8	µs

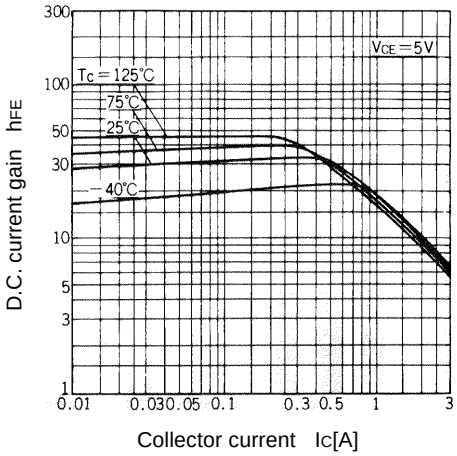
● **Thermal characteristics**

Item	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Thermal resistance	$R_{th(j-c)}$	Junction to case			1.5	°C/W

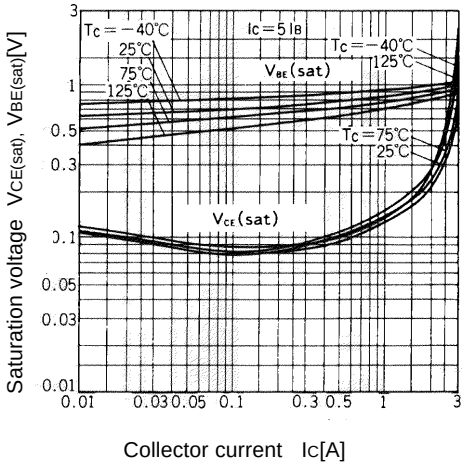
Characteristics



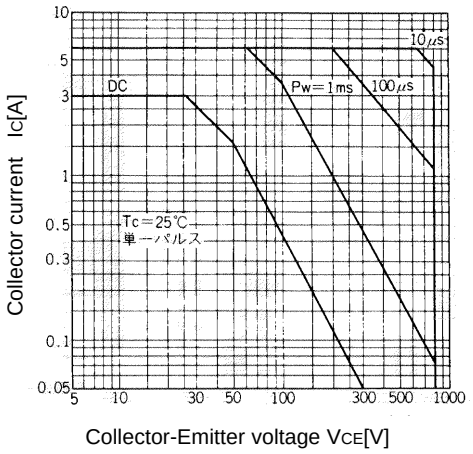
Collector Output Characteristics



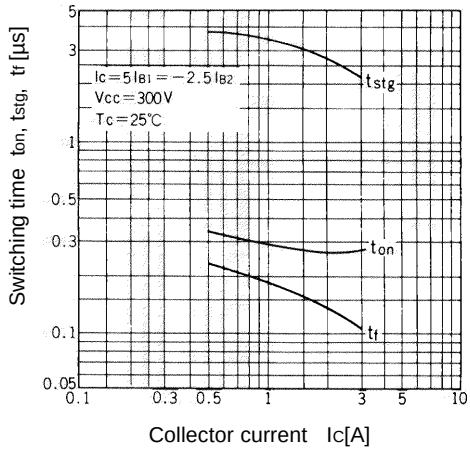
DC Current Gain



Base and Collector Saturation Voltage



Safe Operating Area



Switching Time

***1 Switching Time Test Circuit**